L.
T
5=
1
T
L
Ħ
 s=1
æd,

1	SEMICONDUCTOR DEVICE WITH INDUCTIVE COMPONENT
2	AND METHOD OF MAKING
3	
4	Abstract of the Disclosure
5	
6	An integrated circuit (10) includes a semiconductor
7	substrate (11) that has a top surface (32) for forming a
8	dielectric region (14) with a trench (40) and one or more
9	adjacent cavities (16). A conductive material such as copper
10	is disposed within the trench to produce an inductor (50). A
11	top surface (49) of the inductor is substantially coplanar
12	with an interconnect surface (31) of the semiconductor
13	substrate, which facilitates connecting to the inductor with
14	standard integrated circuit metallization (57).